

Silicon NPN Power Transistors

2SC5200

DESCRIPTION

- With TO-3PL package
- Complement to type 2SA1943

APPLICATIONS

- High current switching
- Recommended for 100W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

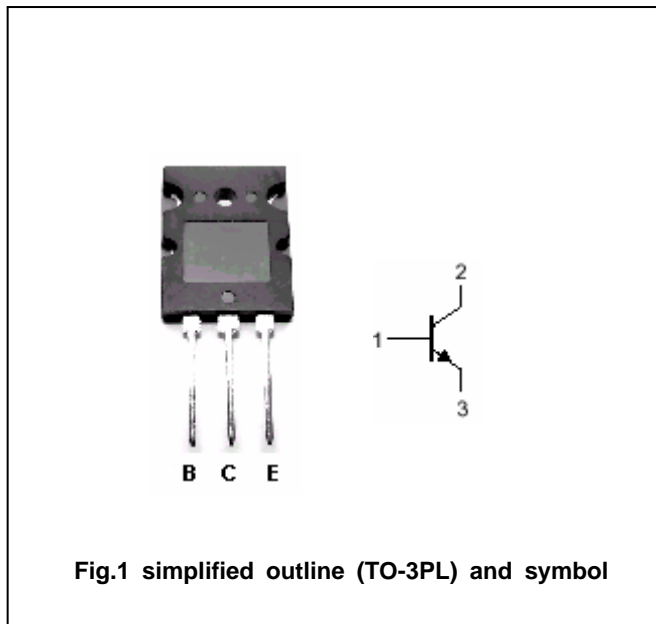


Fig.1 simplified outline (TO-3PL) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	230	V
V_{CEO}	Collector-emitter voltage	Open base	230	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_B	Base current		1.5	A
P_C	Collector power dissipation	$T_C=25$	150	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	230			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A ; I _B =0.8A			3.0	V
V _{BE}	Base-emitter voltage	I _C =7A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =230V; I _E =0			5	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			5	μ A
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	55		160	
h _{FE-2}	DC current gain	I _C =7A ; V _{CE} =5V	35			
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		30		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		200		pF

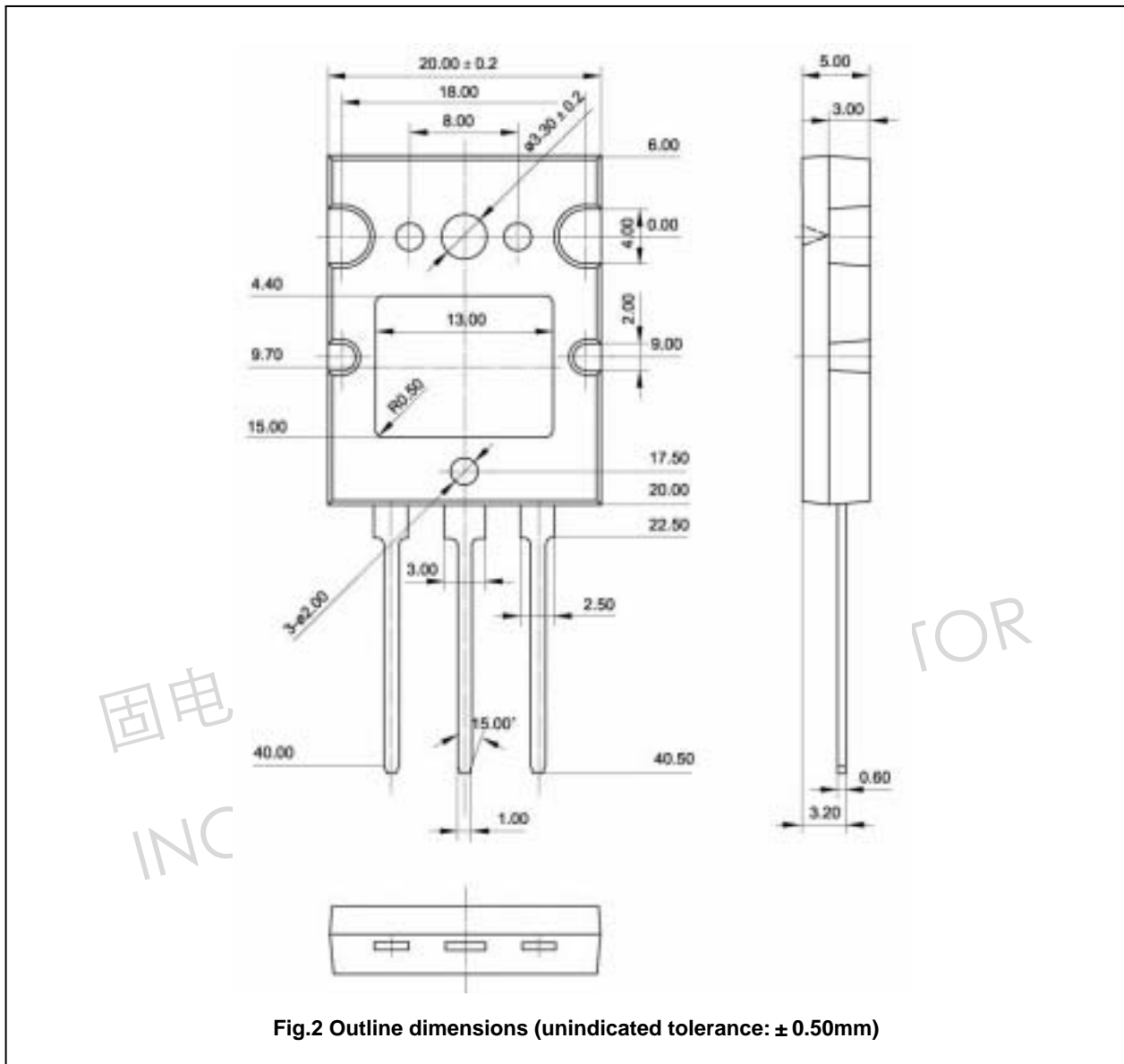
◆ h_{FE-1} classifications

R	O
55-100	80-160

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PACKAGE OUTLINE



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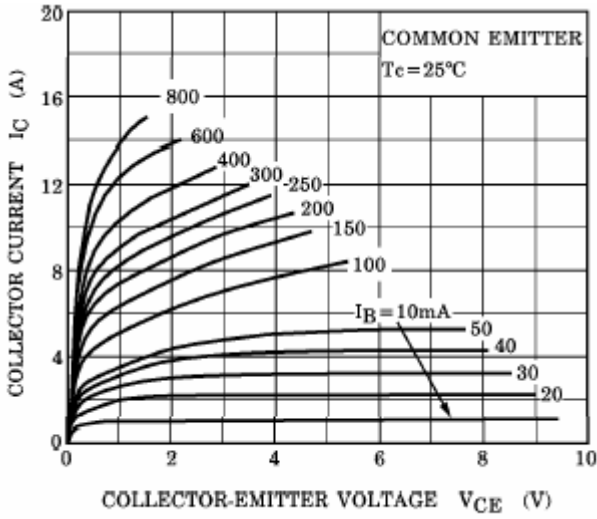


Fig.3 Static Characteristic

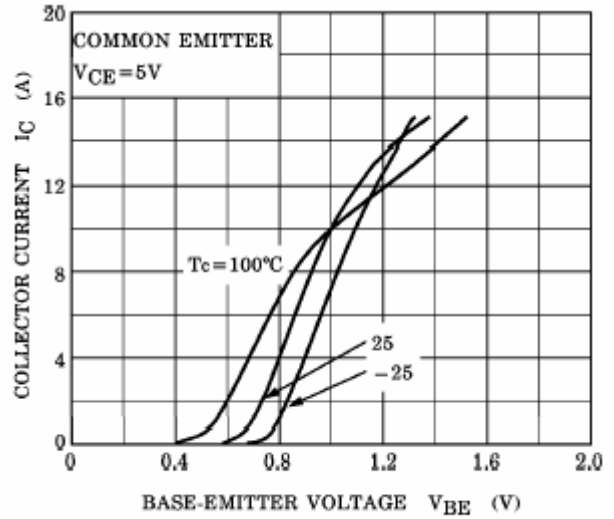


Fig.4 Base-Emitter On Voltage

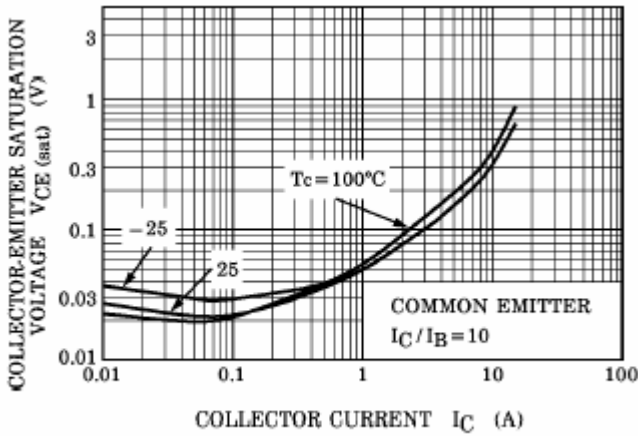


Fig.5 Collector-Emitter Saturation Voltage

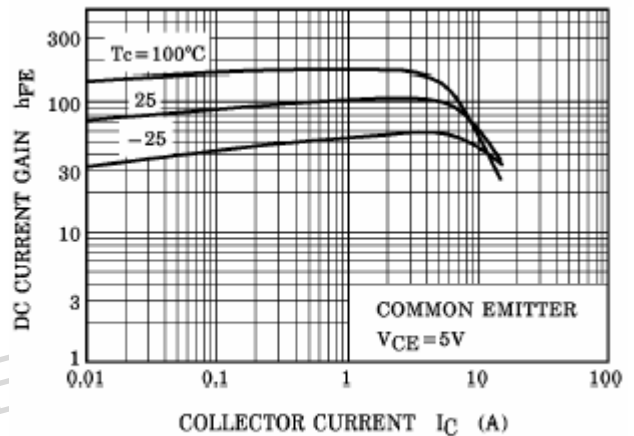


Fig.6 DC current Gain

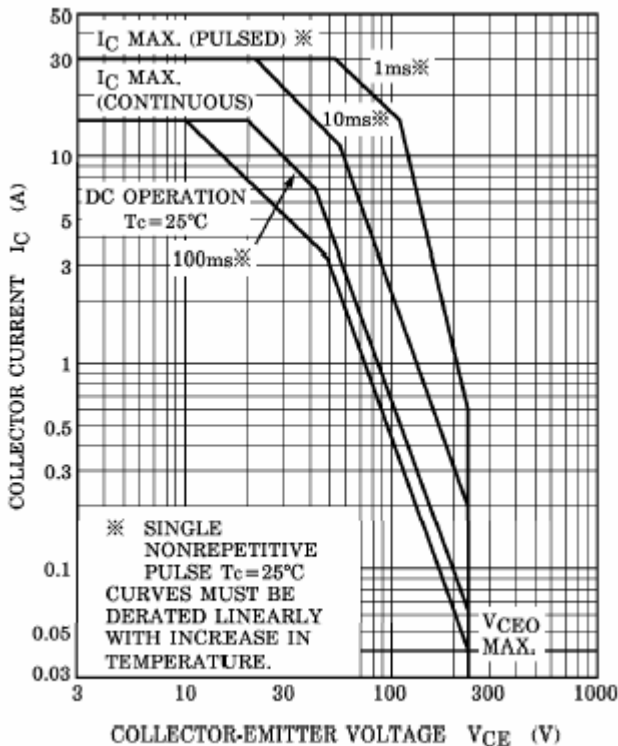


Fig.7 Safe Operating Area